

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

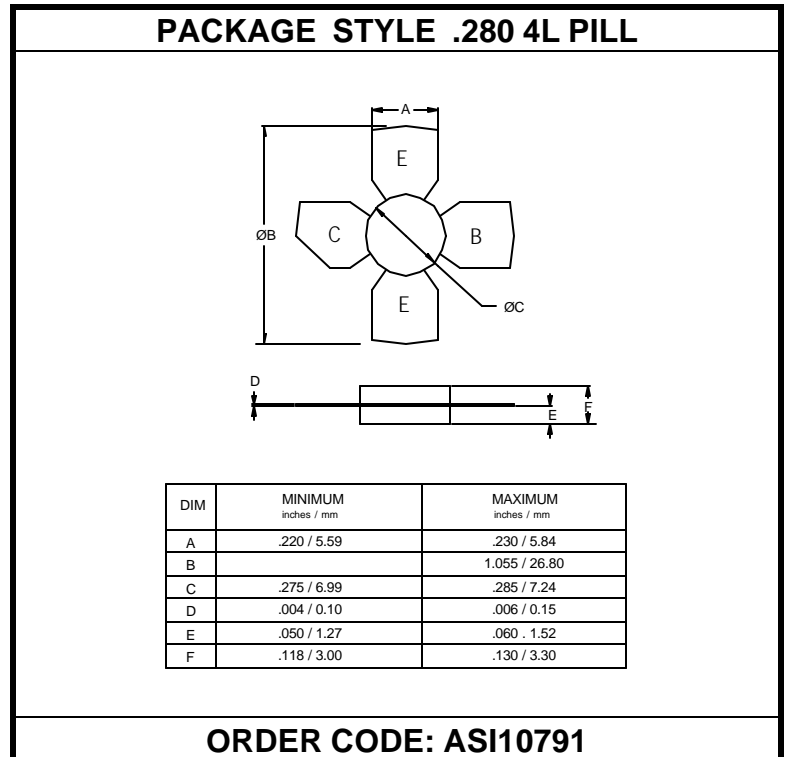
The **C1-28** is Designed for 28 Volt Class C Amplifier Applications up to 500 MHz.

FEATURES:

- $P_G = 12$ dB Typ. at 1.0 W/400 MHz
- $h_C = 65$ % Typ. at 1.0 W/400 MHz
- **Omnigold™** Metalization System

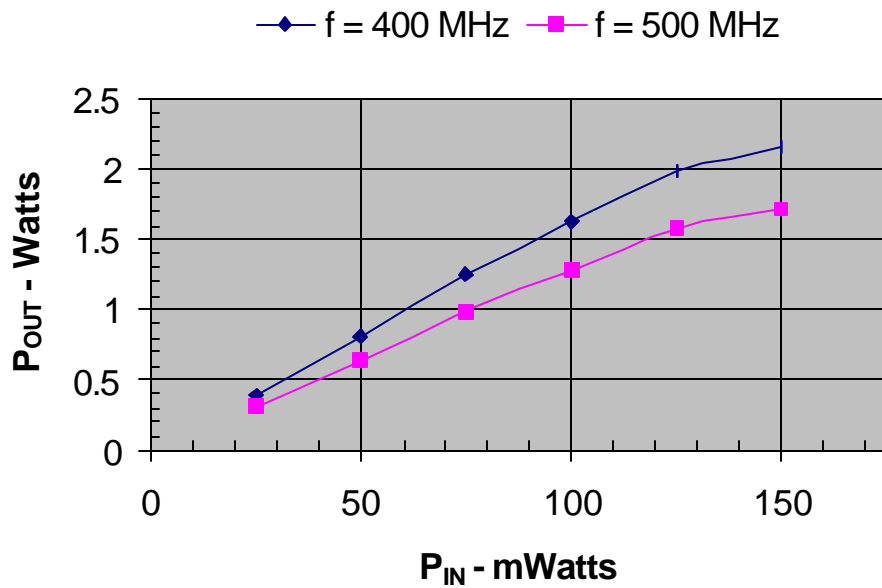
MAXIMUM RATINGS

I_C	250 mA
V_{CBO}	40 V
V_{CEO}	28 V
V_{EBO}	3.5 V
P_{DISS}	7.0 W @ $T_C = 25^\circ C$
T_J	$-65^\circ C$ to $+200^\circ C$
T_{STG}	$-65^\circ C$ to $+150^\circ C$
q_{JC}	$20^\circ C/W$

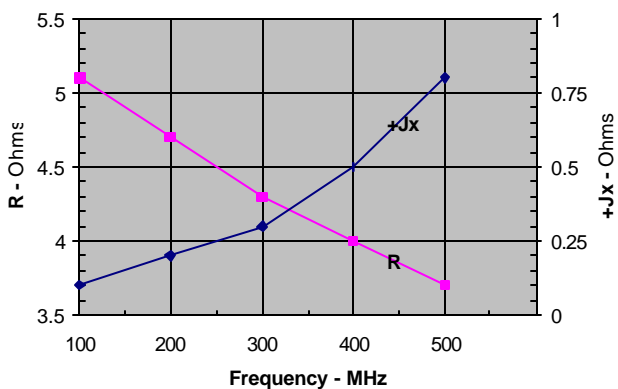

CHARACTERISTICS $T_C = 25^\circ C$

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CBO}	$I_C = 5.0$ mA	50			V
BV_{CES}	$I_C = 5.0$ mA	50			V
BV_{EBO}	$I_E = 5.0$ mA	4.0			V
I_{CBO}	$V_{CB} = 28$ V			500	mA
h_{FE}	$V_{CE} = 5.0$ V $I_C = 100$ mA	20		120	---
C_{OB}	$V_{CB} = 28$ V MHz $f = 1.0$		3.5	5.0	pF
P_G h_C	$V_{CE} = 28$ V $P_{OUT} = 1.0$ W $f = 400$ MHz	10 60	12		dB %

P_{IN} vs. P_{OUT}



Series Input Impedance
R + jX



Series Load Impedance
R + jX

